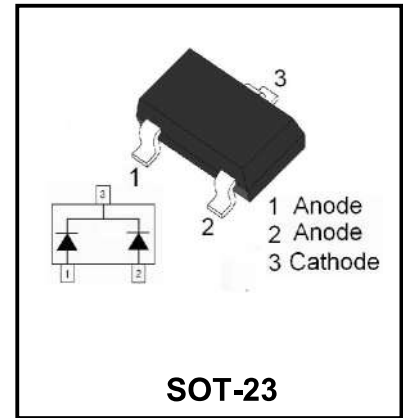


**Dual Switching Diode Common Cathode**

**Features**

- High Conductance:  $I_F = 100\text{ mA}$
- Fast Switching Speed:  $t_{rr} < 4\text{ ns}$  Maximum
- Small Plastic SOT-23 Package



**Product Specification Classification**

Part Number	Package	Marking	Pack
DAN202K	SOT-23	N	3000PCS/Tape

**Absolute Maximum Ratings (Ta=25°C)**

Parameter	Symbol	Values	Units
Reverse Voltage	$V_R$	80	V
Forward current	$I_F$	100	mA
Peak Forward Surge Current	$I_{FM(surge)}$	300	mA
Power dissipation $T_S \leq 55\text{ °C}$	$P_D$	200	mW
Operating temperature range	$T_j$	-55~150	°C
Storage Temperature Range	$T_{stg}$	-55~150	°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	K/W

**Electrical Characteristics (Ta=25°C Unless otherwise noted )**

Parameter	Symbol	Test Conditions	Min.	Typ	Max.	Units
<b>DC Characteristics</b>						
Breakdown Voltage, per Diode	$V_R$	$I_R = 100\mu\text{A}$	80			V
Forward voltage, per Diode	$V_F$	$I_F = 1\text{ mA}$			0.7	V
		$I_F = 10\text{ mA}$			0.8	
		$I_F = 50\text{ mA}$			1.0	
		$I_F = 100\text{ mA}$			1.2	
Reverse Leakage, per Diode	$I_R$	$V_R = 70\text{V}$			0.1	$\mu\text{A}$
Total Capacitance, per Diode	$C_T$	$V_R = 6\text{ V}, f = 1.0\text{ MHz}$			3.5	pF
Reverse-Recovery Time, per Diode	$t_{rr}$	$V_R = 6\text{V}, I_F = 5\text{mA}$			4	ns

Typical Characteristic

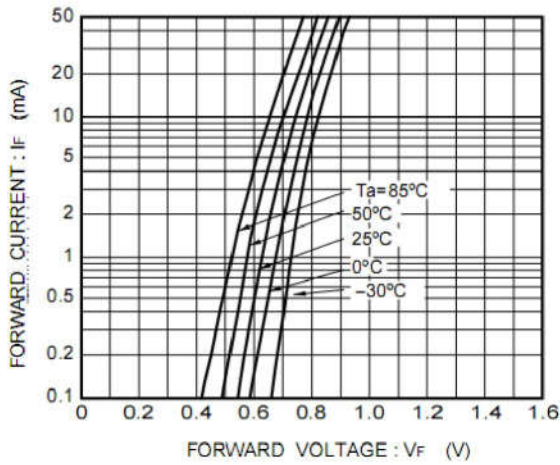


Figure 1. Forward characteristics

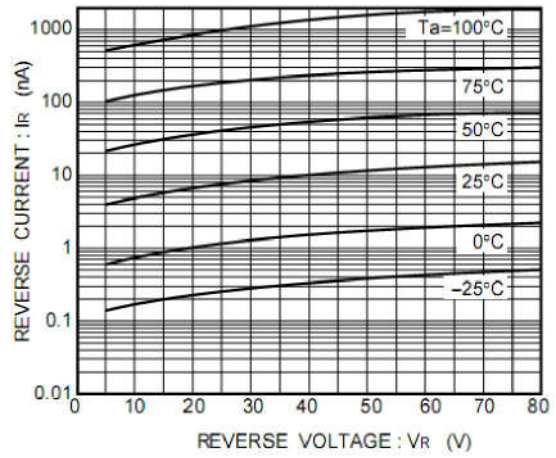


Figure 2. Reverse characteristics

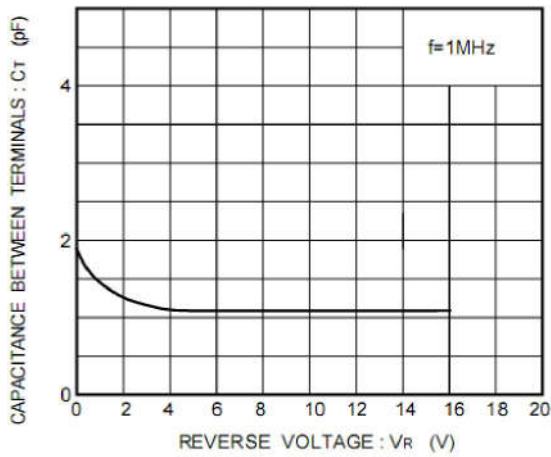


Figure 3. Capacitance between terminals characteristics

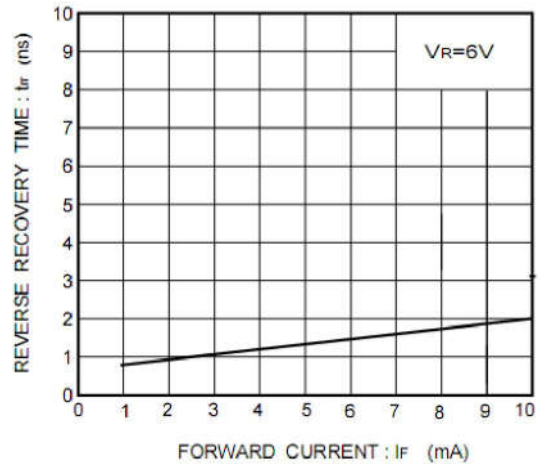


Figure Reverse recovery time

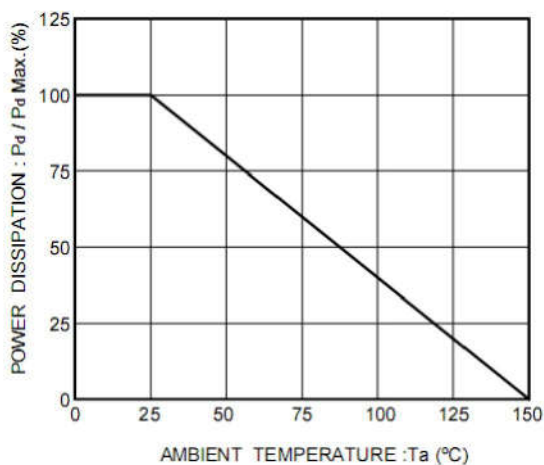


Figure 5. Power attenuation curve

Package Dimensions

Symbol	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	0.90	1.15	0.035	0.045
A1	0.00	0.10	0.000	0.004
A2	0.90	1.05	0.035	0.041
b	0.30	0.50	0.012	0.020
c	0.08	0.15	0.003	0.006
D	2.80	3.00	0.110	0.118
E	1.20	1.40	0.047	0.055
E1	2.25	2.55	0.089	0.100
e	0.90	1.00	0.035	0.039
e1	1.80	2.00	0.071	0.079
L	0.50	0.60	0.020	0.024
L1	0.30	0.50	0.012	0.020